

### **BD243/A/B/C**

# Medium Power Linear and Switching Applications

• Complement to BD244, BD244A, BD244B and BD244C respectively



1.Base 2.Collector 3.Emitter

Rev. A, February 2000

# **NPN Epitaxial Silicon Transistor**

### Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage		
	: BD243	45	V
	: BD243A	60	V
	: BD243B	80	V
	: BD243C	100	V
V <sub>CEO</sub>	Collector-Emitter Voltage		
	: BD243	45	V
	: BD243A	60	V
	: BD243B	80	V
	: BD243C	100	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current (DC)	6	Α
I <sub>CP</sub>	*Collector Current (Pulse)	10	А
I <sub>B</sub>	Base Current	2	Α
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	65	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 65 ~ 150	°C

### Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V <sub>CEO</sub> (sus)	* Collector-Emitter Sustaining Voltage					
	: BD243	$I_C=30$ mA, $I_B=0$	45			V
	: BD243A		60			V
	: BD243B		80			V
	: BD243C		100			V
I <sub>CEO</sub>	Collector Cut-off Current : BD243/243A	$V_{CE} = 30V, I_{B} = 0$			0.7	mA
	: BD243B/243C	$V_{CE} = 60V, I_{B} = 0$			0.7	mA
I <sub>CES</sub>	Collector Cut-off Current : BD243	$V_{CE} = 45V, V_{BE} = 0$			0.4	mA
	: BD243A	$V_{CE} = 60V, V_{BE} = 0$			0.4	mA
	: BD243B	$V_{CE} = 80V, V_{BE} = 0$			0.4	mA
	: BD243C	$V_{CE} = 100V, V_{BE} = 0$			0.4	mA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			1	mA
h <sub>FE</sub>	*DC Current Gain	$V_{CE} = 4V, I_{C} = 0.3A$	30			
		$V_{CE} = 4V, I_{C} = 3A$	15			
V <sub>CE</sub> (sat)	*Collector-Emitter Saturation Voltage	$I_C = 6A, I_B = 1A$			1.5	V
V <sub>BE</sub> (on)	*Base-Emitter ON Voltage	$V_{CE} = 4V, I_{C} = 6A$			2	V
Pulse Test :PW=3		•	•	•	1	•

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# **Typical Characteristics**

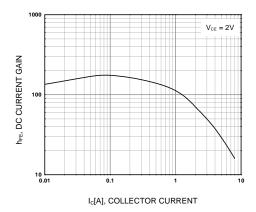


Figure 1. DC current Gain

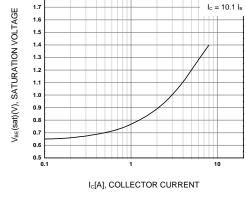


Figure 2. Base-Emitter Saturation Voltage

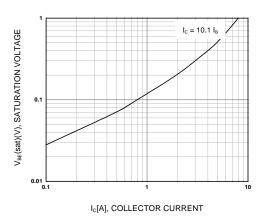


Figure 3. Collector-Emitter Saturation Voltage

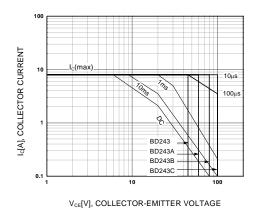


Figure 4. Safe Operating Area

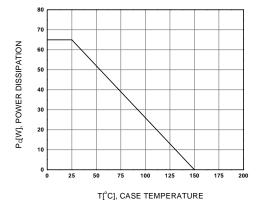
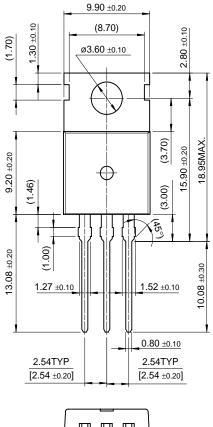


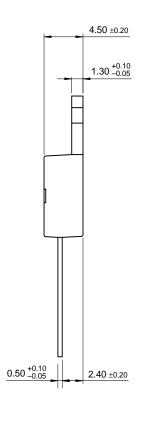
Figure 5. Power Derating

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# **Package Demensions**

# TO-220





10.00 ±0.20

Dimensions in Millimeters

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